

### Description

The HSBB6214 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

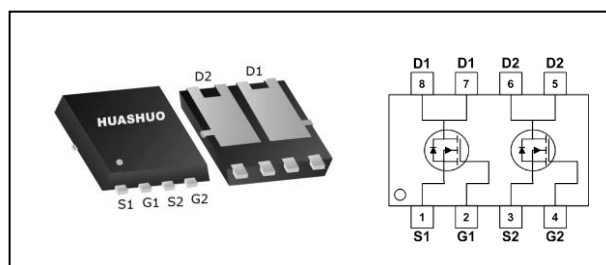
The HSBB6214 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

### Product Summary

$V_{DS}$	60	V
$R_{DS(ON),MAX}$	42	m $\Omega$
$I_D$	16	A

### PRPAK3\*3 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	16	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	10	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	4.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	3.6	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	32	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	22	mJ
$I_{AS}$	Avalanche Current	21	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	1.7	W
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	21	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	6	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.044	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	---	---	42	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	---	52	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.7	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.8	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	---	28	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.5	---	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =48V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A	---	19	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.6	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	4.1	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =4A	---	3	---	ns
T <sub>r</sub>	Rise Time		---	34	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	23	---	
T <sub>f</sub>	Fall Time		---	6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	1027	---	pF
C <sub>oss</sub>	Output Capacitance		---	65	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	46	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	16	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =4A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	12.1	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	6.7	---	nC

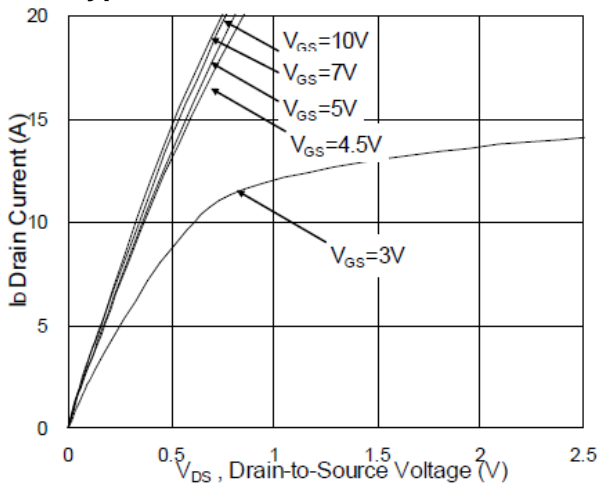
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=21A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

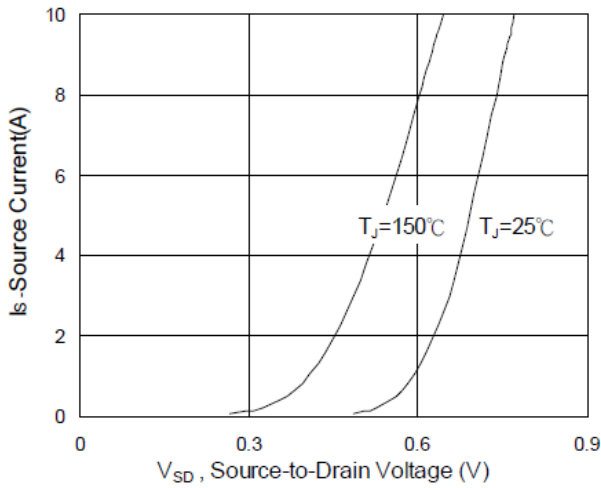


## Dual N-Ch 60V Fast Switching MOSFETs

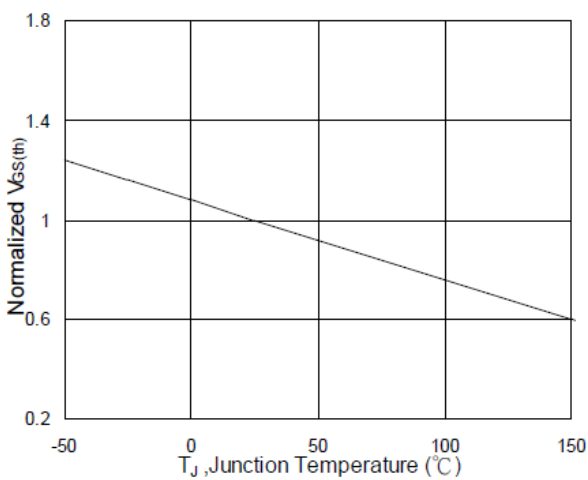
### Typical Characteristics



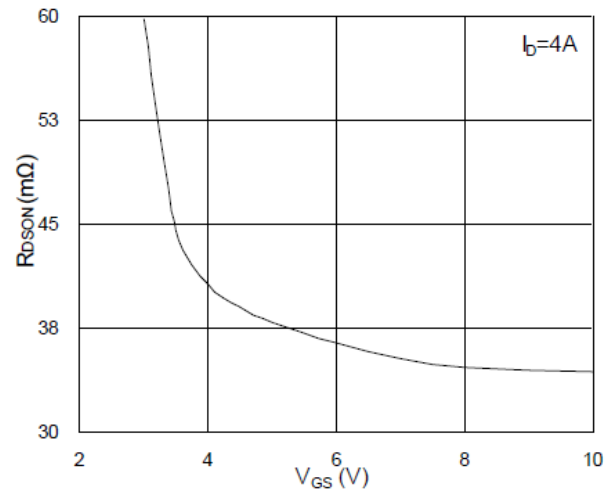
**Fig.1 Typical Output Characteristics**



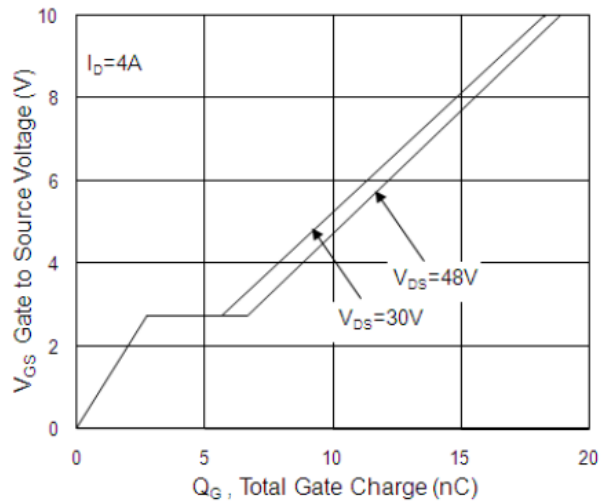
**Fig.3 Forward Characteristics Of Reverse**



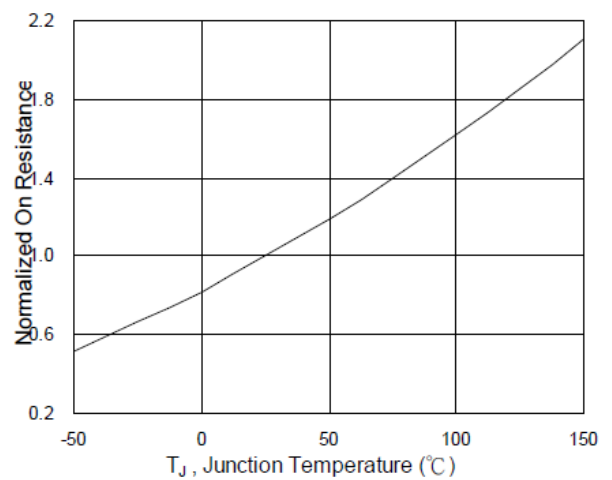
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



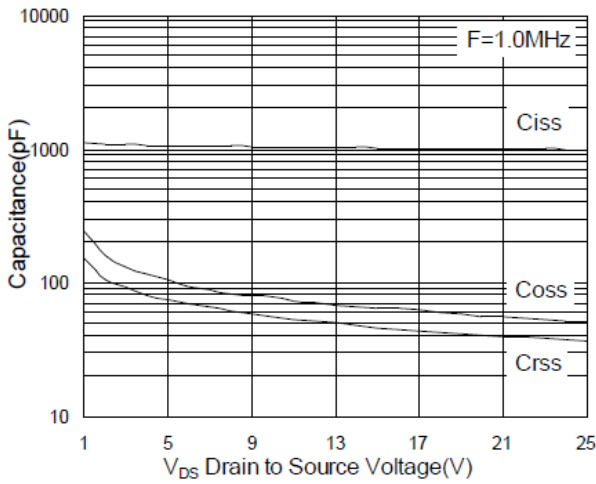
**Fig.2 On-Resistance vs. Gate-Source**



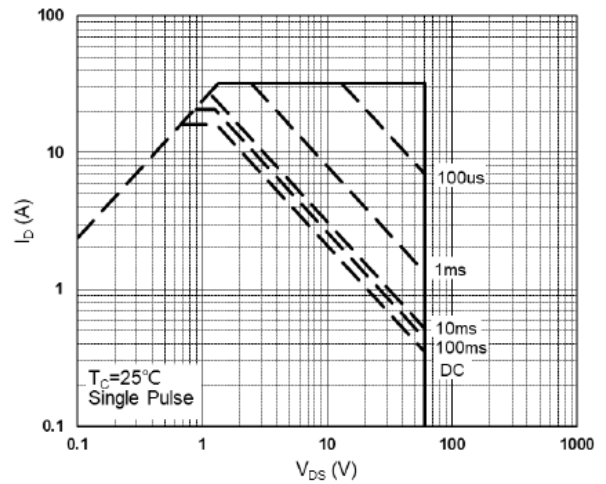
**Fig.4 Gate-Charge Characteristics**



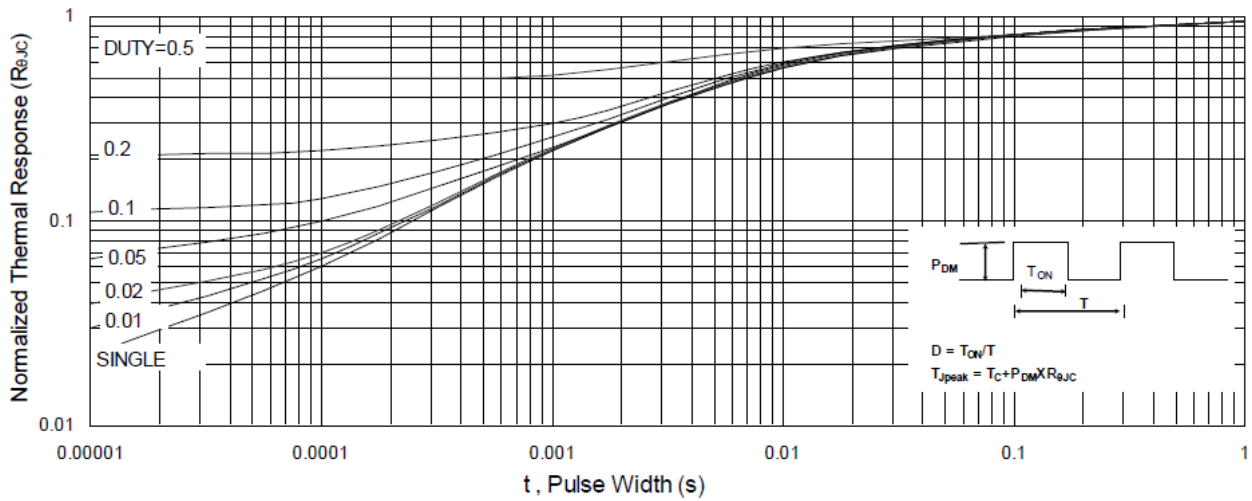
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



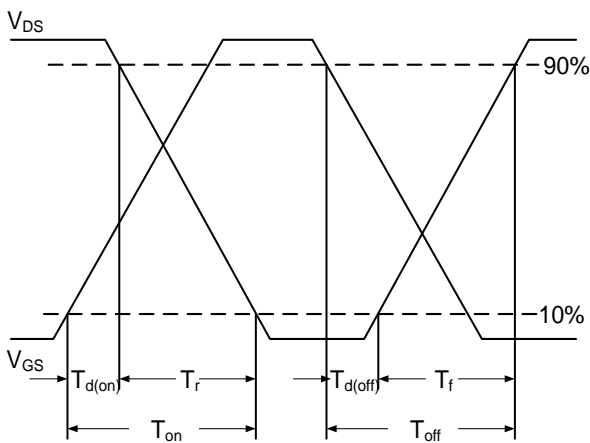
**Fig.7 Capacitance**



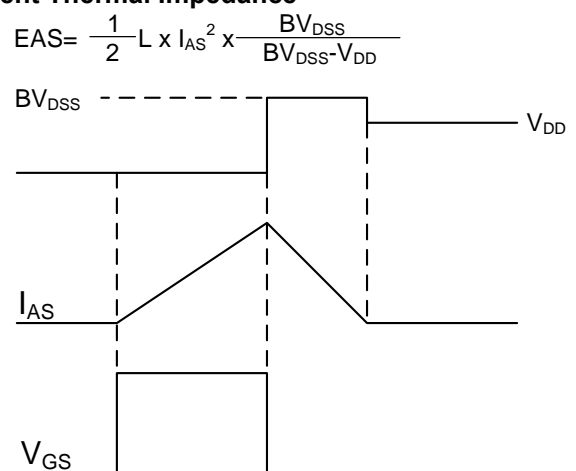
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching**